

## 1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) surface mountable plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series B" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

## 3. Applications

- Heating controls
- High power motor control
- High power switching

## 4. Quick reference data

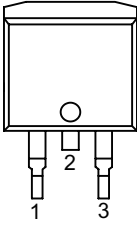
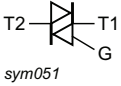
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 91\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	25	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	190	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	209	A
$T_j$	junction temperature		-	-	125	°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_2 + G+$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	2	18	50	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	2	21	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	2	34	50	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	31	60	mA
$V_T$	on-state voltage	$I_T = 30\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	1,3	1.55	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	4000	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 12</a>	-	44	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

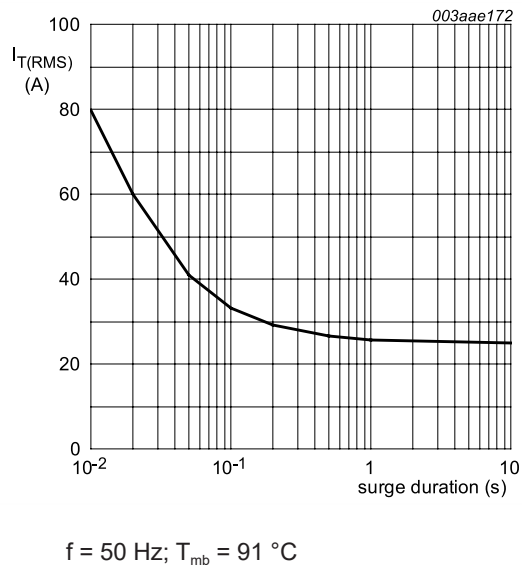
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA225B-800B	TO263	BTA225B-800B,118	Reel	800	TO263E	26-May-2017

## 7. Limiting values

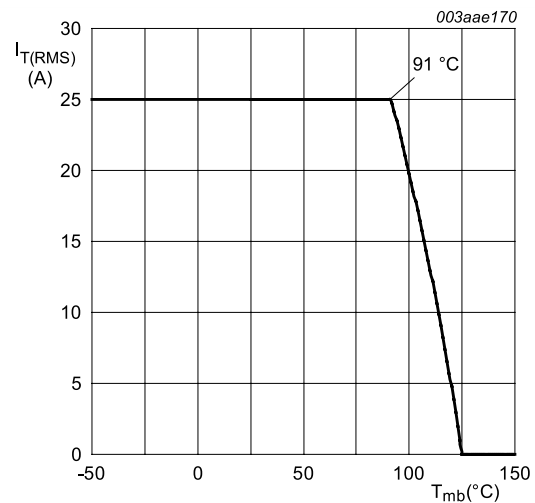
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage			-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 91\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		-	25	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>		-	190	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$		-	209	A
$I^2t$	$I^2t$ for fusing	$t_{\text{p}} = 10\text{ ms}$ ; SIN		-	180	$\text{A}^2\text{s}$
$di_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{G}} = 100\text{ mA}$		-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current			-	2	A
$P_{\text{GM}}$	peak gate power			-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.5	W
$T_{\text{stg}}$	storage temperature			-40	150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature			-	125	$^{\circ}\text{C}$



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values**

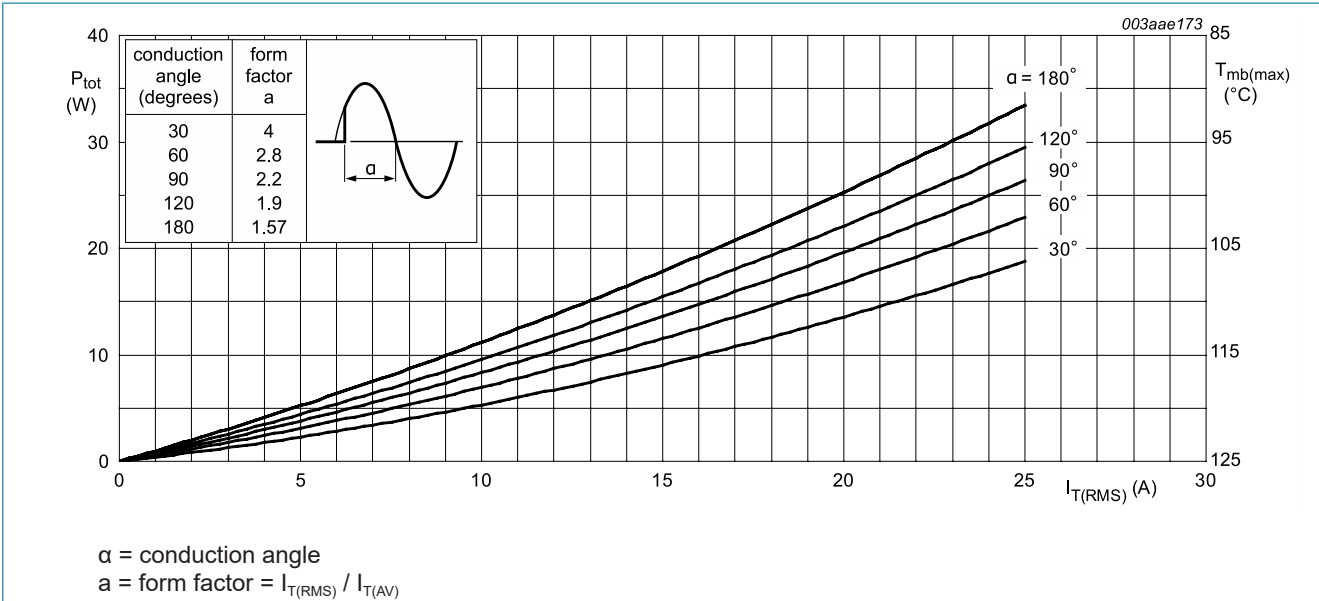


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

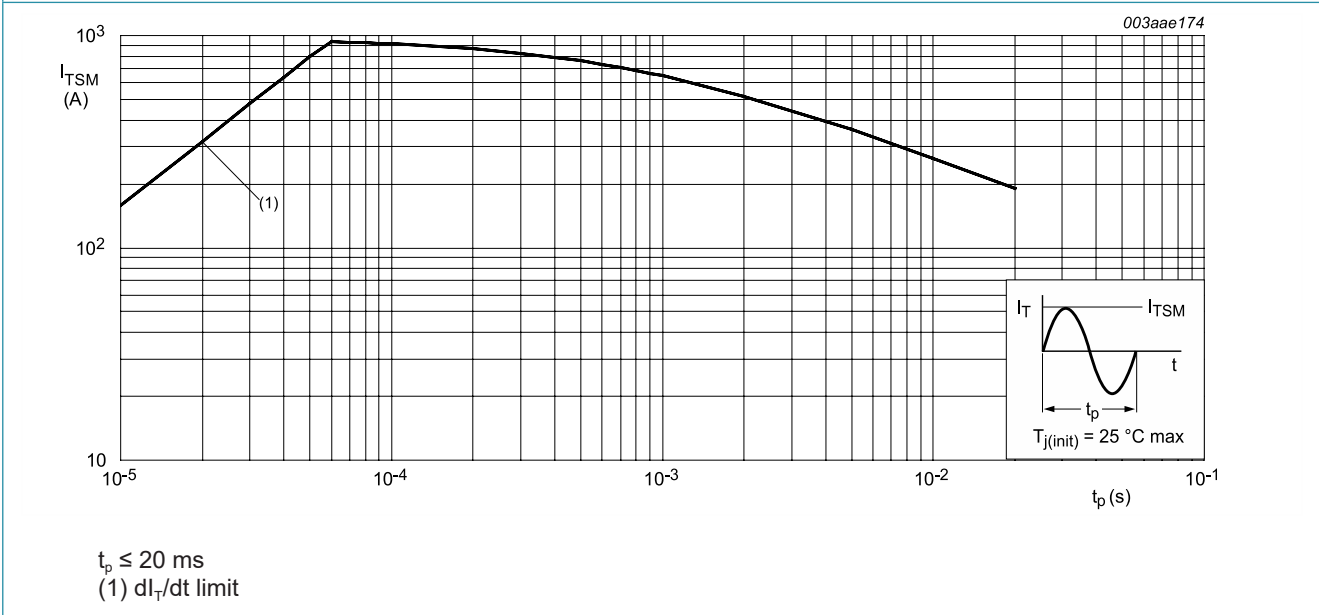


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

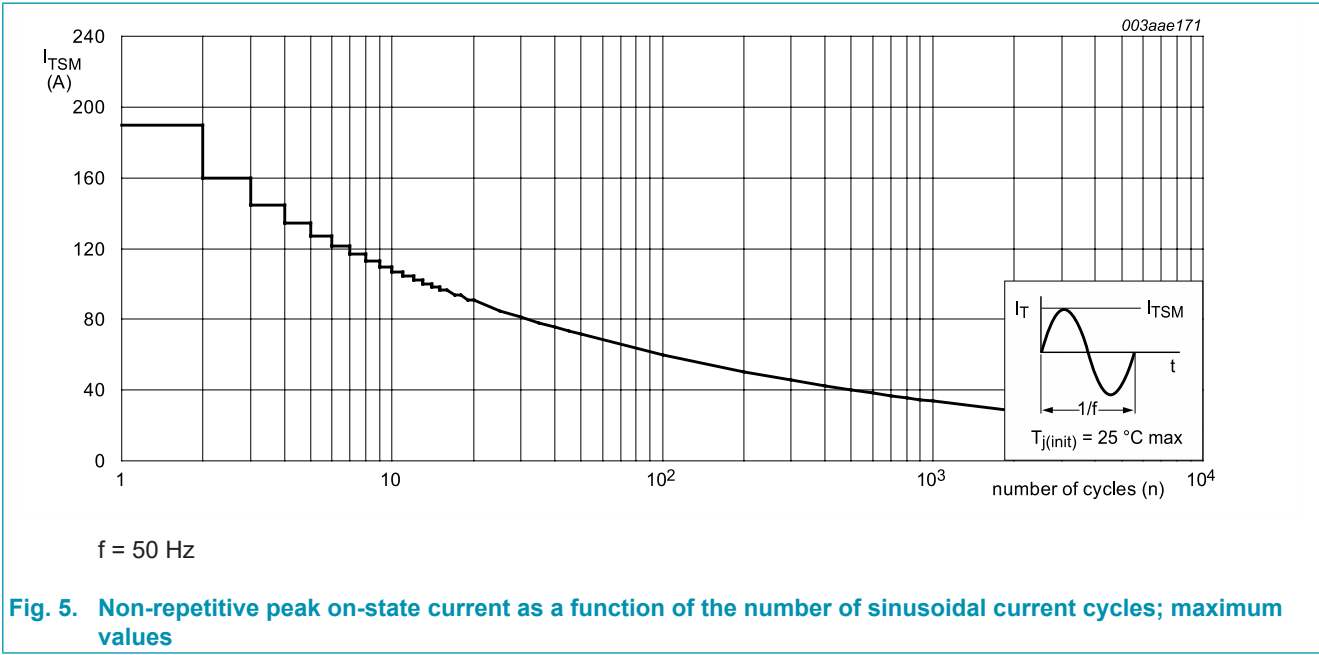


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1	K/W
		half cycle; Fig. 6	-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W

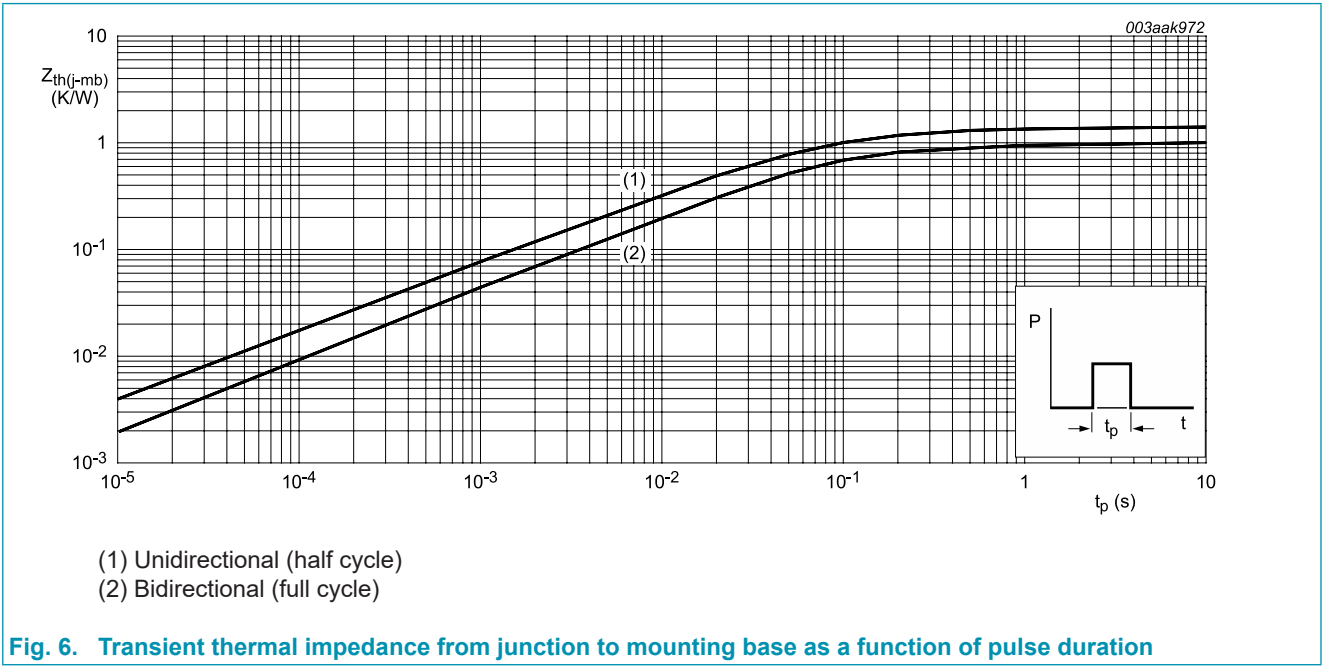
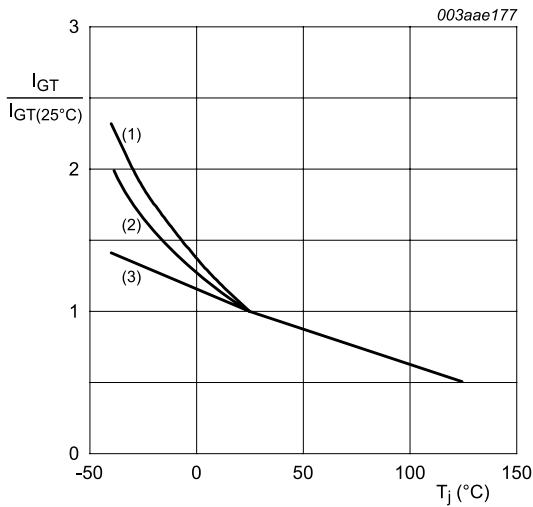


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>		2	18	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>		2	21	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>		2	34	50	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>		-	31	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>		-	34	90	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>		-	30	60	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>		-	31	60	mA
$V_T$	on-state voltage	$I_T = 30\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>		-	1,3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 11</a>		-	0.7	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 125\text{ °C}$ ; <a href="#">Fig. 11</a>		0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 125\text{ °C}$		-	0.1	0.5	mA
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		1000	4000	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_J = 125\text{ °C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu$ s; gate open circuit; <a href="#">Fig. 12</a>		-	44	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

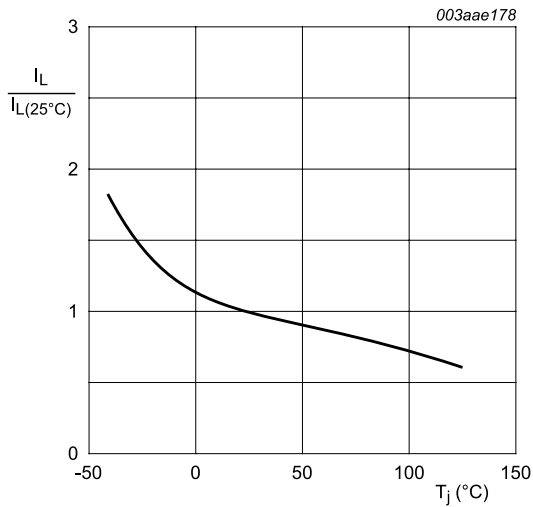


Fig. 8. Normalized holding current as a function of junction temperature

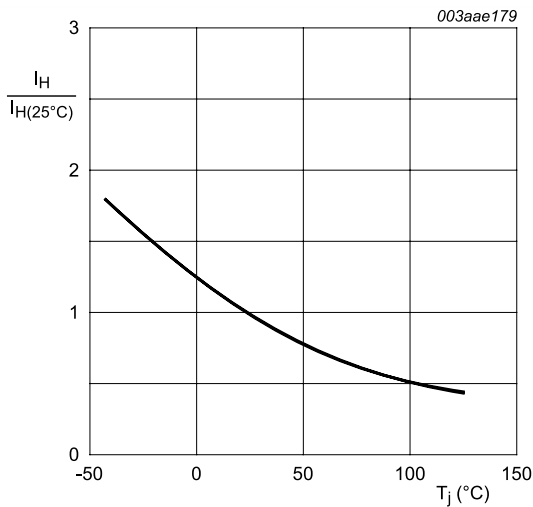
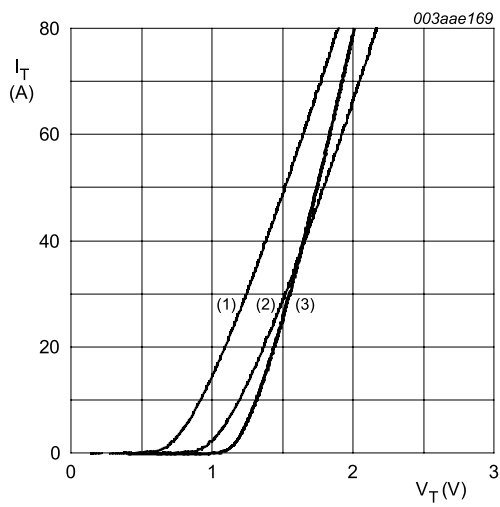


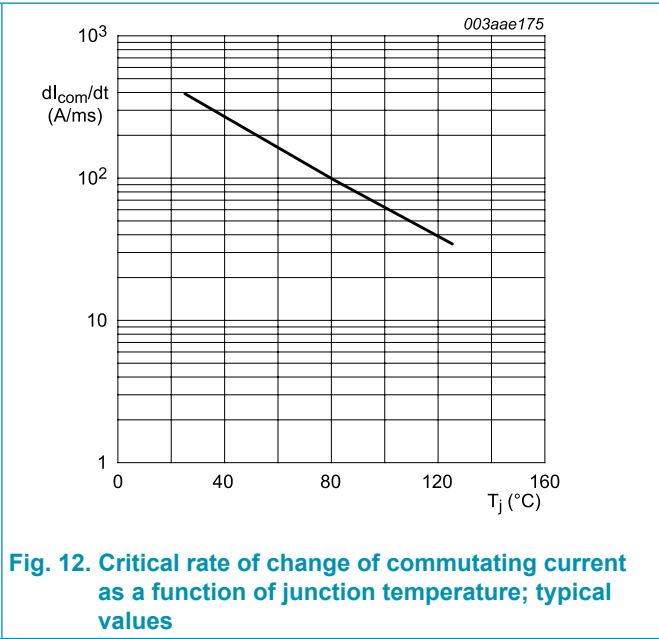
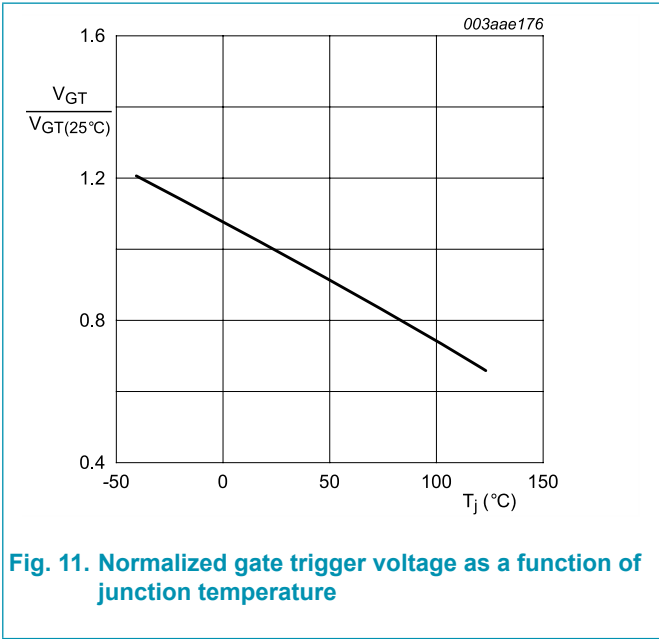
Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.073 \text{ V}$ ;  $R_s = 0.015 \Omega$
- (1)  $T_j = 125^{\circ}\text{C}$ ; typical values
  - (2)  $T_j = 125^{\circ}\text{C}$ ; maximum values
  - (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

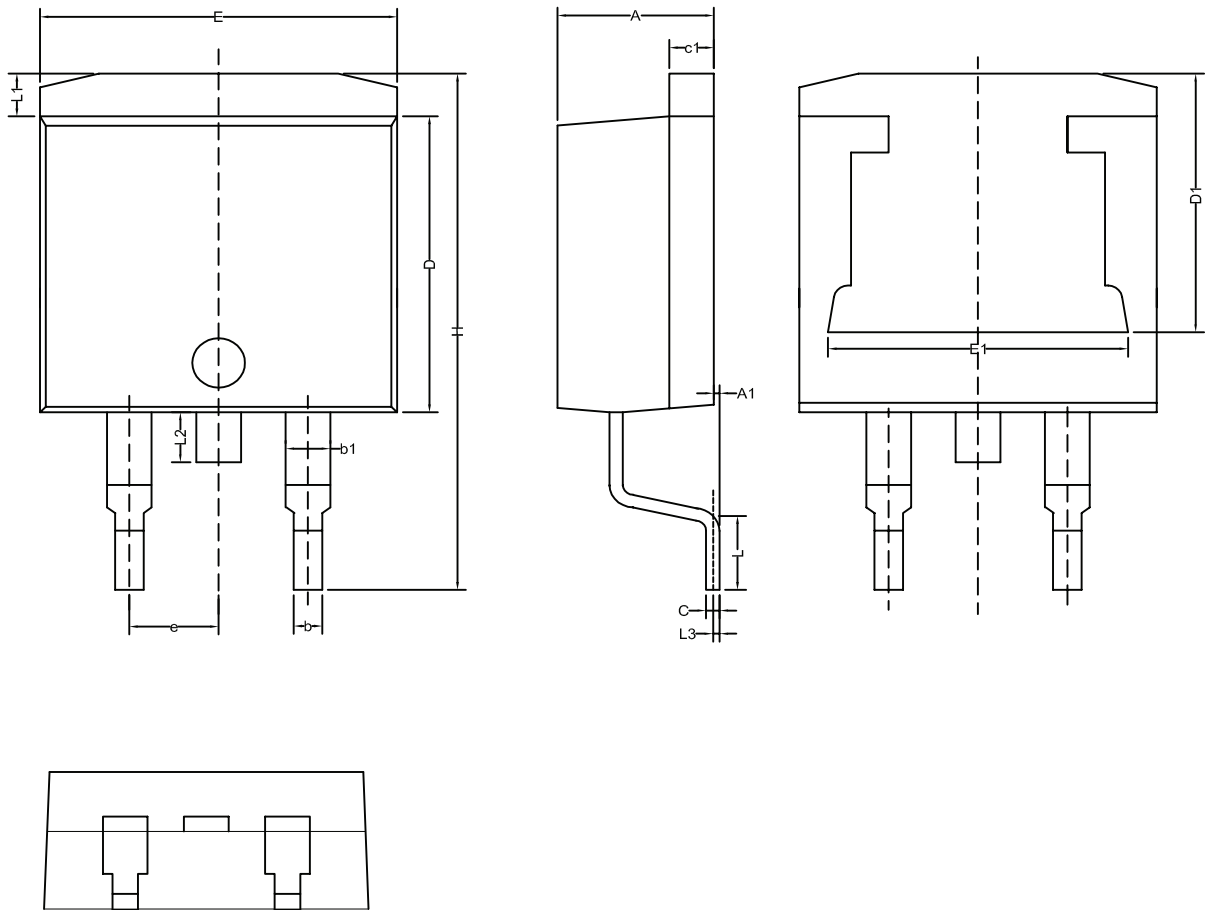
Fig. 10. On-state current as a function of on-state voltage





10. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



Unit	A	A1	b	b1	c	c1	D	D1	E	E1	e	H	L	L1	L2	L3
MM	min	4.35	0.00	0.69	1.14	0.38	1.14	8.50	7.50	10.00	8.25	14.60	2.50	1.00	1.27	
	max	4.75	0.15	0.99	1.73	0.61	1.40	9.02	8.00	10.40	8.80	15.60	2.79	1.65	1.78	0.25 (BSC.)

## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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